

Magnetic Replacement Ballast IC

Features

- Ballast control plus half-bridge driver in one IC
- Single-stage topology (no PFC stage required)
- High PF and low THD
- Preheat, ignition and running lamp modes
- Closed-loop lamp current control
- Half-bridge NZVS protection
- Adaptive dead-time
- Lamp insert auto-restart
- Internal bootstrap MOSFET
- Micro-power start-up current
- 15.6V internal zener clamp on VCC
- Excellent ESD and latch immunity
- · RoHS compliant
- 8-pin SO8 package

Applications

- Magnetic replacement electronic ballast
- Low cost electronic ballast

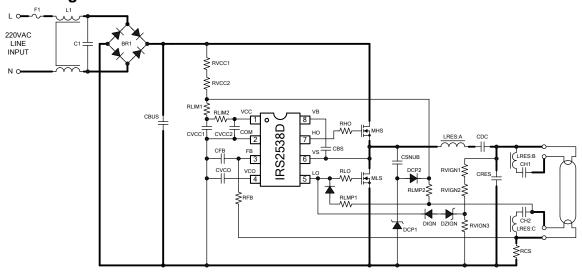
Description

This IC takes full advantage of IR's patented ballast and high-voltage technologies to realize a simple, highperformance magnetic ballast replacement solution. The IC includes a novel single-stage circuit topology and control method to achieve high power factor and low THD without a PFC stage or any electrolytic capacitors. A single high-voltage pin senses the halfbridge voltage to perform necessary protection functions. Closed-loop control of the lamp current provides constant lamp brightness over a wide line input voltage range. Combining these high-voltage control algorithms in a single 8-pin IC results in a large reduction in component count, an increase in manufacturability and reliability, a reduced design cycle time. while maintaining high ballast system performance.

Package Options



Application Diagram



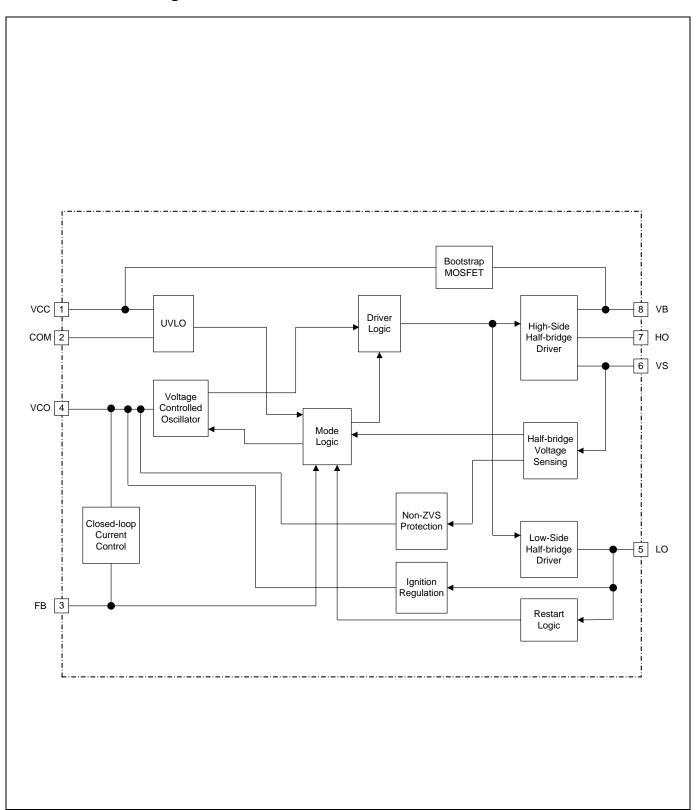
Ordering Information

Base Part Number	Packago Typo	Standar	d Pack	Orderable Part Number	
Dase Fait Number	Package Type	Form Quantity		Orderable Part Number	
IRS2538DSPBF	SO8N	Tape and Reel	2500	IRS2538DSTRPBF	

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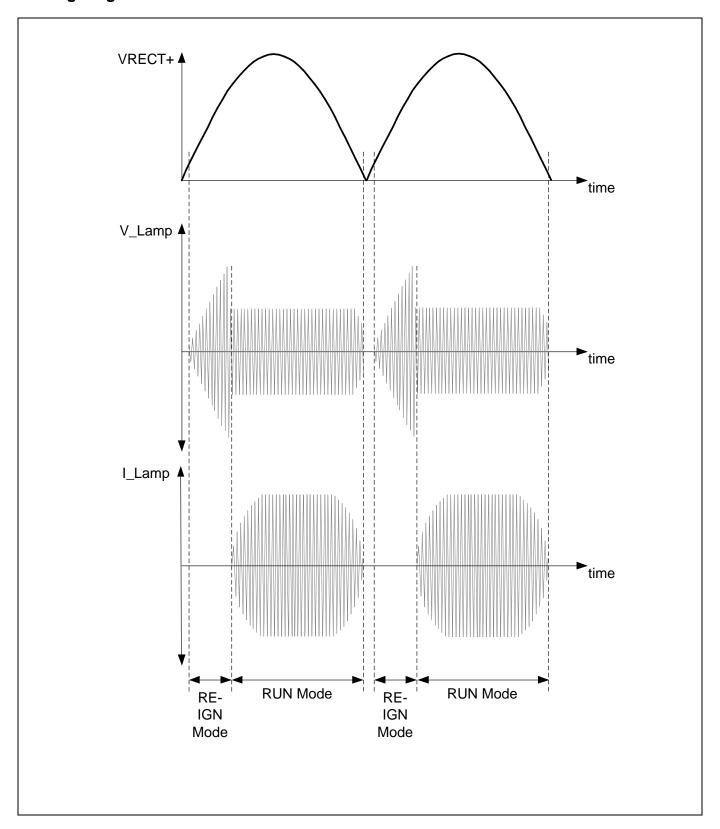


Functional Block Diagram





Timing Diagram



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Qualification Information[†]

Qualification info	mation				
		Industrial [™] (per JEDEC JESD 47E)			
Qualification Level		Comments: This family of ICs has passed JEDEC's Industrial qualification. IR's Consumer qualification level is granted by extension of the higher Industrial level.			
Moisture Sensitivity L	_evel	SOIC8N MSL2 ^{†††} (per IPC/JEDEC J-STD-0200			
ESD	Machine Model	(per JEDEC	Class A standard EIA/JESD22-A115-A)		
E3D	Human Body Model	(per EIA/JED	Class IC DEC standard JESD22-A114-B)		
IC Latch-Up Test		Class I, Level A			
10 _u.u. op 1001			(per JESD78A)		
RoHS Compliant		Yes			

- † Qualification standards can be found at International Rectifier's web site http://www.irf.com/
- †† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information.
- ††† Higher MSL ratings may be available for the specific package types listed here. Please contact your International Rectifier sales representative for further information.

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Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any pin. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
VB	High-Side Floating Supply Voltage	-0.3	625	
VS	High-Side Floating Supply Offset Voltage	VB - 25	VB + 0.3	
VHO	High-Side Floating Output Voltage	VS - 0.3	VB + 0.3	V
VLO	Low-Side Output Voltage	-0.3	VCC + 0.3	
Vvco	VCO Input Voltage	-0.3	6	
VFB	FB Input Voltage	-0.3	VCC + 0.3	
ICC	Supply Current [†]		20	
IOMAX	Maximum allowable current at LO, HO and PFC due to external power transistor Miller effect.	-500	500	mA
dV _s /dt	Allowable VS Pin Voltage Slew Rate	-50	50	V/ns
PD	Maximum Power Dissipation @ T _A ≤ +25°C, 8-Pin SOIC		0.625	W
R_{θ} JA	Thermal Resistance, Junction to Ambient, 8-Pin SOIC		128	°C/W
TJ	Junction Temperature	-55	150	
TS	Storage Temperature	-55	150	°C
TL	Lead Temperature (Soldering, 10 seconds)		300	

^{†:} This IC contains a voltage clamp structure between the chip VCC and COM which has a nominal breakdown voltage of 15.6V. This supply pin should not be driven by a DC, low impedance power source greater than the VCLAMP specified in the Electrical Characteristics section.



Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions.

Symbol	Definition	Min.	Max.	Units
VBS	High-Side Floating Supply Voltage	VCC - 0.7	VCLAMP	V
VS	Steady State High-Side Floating Supply Offset Voltage	-3.0 ^{††}	600	V
VCC	Supply Voltage	VCCUV+ + 0.1V	VCLAMP	V
ICC	Supply Current	†††	5	mA
TJ	Junction Temperature	-40	125	°C

- ††: Care should be taken to avoid output switching conditions where the VS node rings below COM by more than 5V.
- †††: Enough current should be supplied to the VCC pin of the IC to keep the internal 15.6V zener diode regulating at its voltage, VCLAMP.



Electrical Characteristics

VCC=VBS=14V, VS=0V and TA = 25°C unless otherwise specified. The output voltage and current (VO and IO) parameters are referenced to COM and are applicable to the respective HO and LO output pins.

Symbol	Definition		Тур	Max	Units	Test Conditions		
Low Voltage Supply Characteristics								
VCLAMP	V _{CC} Zener Clamp Voltage	14.5	15.5	16.5		I _{CC} = 10mA		
Vccuv+	Rising Vcc UVLO Threshold	11.2	11.8	12.3	V			
Vccuv-	Falling V _{CC} UVLO Threshold	8.5	9.0	9.5	ď			
Vccuvhys	V _{CC} UVLO Hysteresis		2.8					
laccuv	Micro-power Startup V _{CC} Supply Current			125	μΑ	VCC = Vccuv+ - 500mV		
I CCfmin	f _{MIN} V _{CC} Supply Current		2.2		- A	VCO ≥ 5V		
ICCfmax	f _{MAX} V _{CC} Supply Current		3.2		mA	VCO = 0V		
IQCCFLT	Fault Mode V _{CC} Supply Current			300	μA	MODE = FAULT, Vcc = Vccuv+		
Floating S	upply Characteristics							
IQBS	Quiescent V _{BS} Supply Current		28		μA			
V _{BSUV+}	Rising V _{BS} Supply UVLO Threshold		7.2		V			
V _{BSUV} -	Falling V _{BS} Supply UVLO Threshold		6.8		V			
I _{LK}	Offset Supply Leakage Current			170	μА	$V_{B} = V_{S} = 600V$		
Ballast Co	ntrol Characteristics							
fmin	Minimum Output Frequency	17.4	18.3	19.4	1.11=	VCO ≥ 5V		
f _{MAX}	Maximum Output Frequency	80.9	85.6	91.3	kHz	VCO = 0V		
d	Duty Cycle		50		%			
DT _{MIN}	Minimum Output Dead-time (HO or LO) 0.48							
DT _{MAX}	Maximum Output Dead-time (HO or LO)		1.35		μs			
VLOSD+	LO Pin Shutdown Threshold 13.3 LO Pin Re-start Threshold 11.1				MODE = FAULT			
V _{LOSD} -				IVIODE = FAULT				
VLORSTHYS	LO Pin Restart Hysteresis		2.2		V			
Vzvsth	VS Non-ZVS Detection Threshold		4.6			LO = HIGH		



Electrical Characteristics

VCC=VBS=14V, VS=0V and TA = 25°C unless otherwise specified. The output voltage and current (VO and IO) parameters are referenced to COM and are applicable to the respective HO and LO output pins.

Symbol	Definition	Min	Тур	Max	Units	Test Conditions			
PREHEAT	PREHEAT Mode Characteristics								
T _{PH}	Post of Time		2.0			f _{Line} = 60Hz, GBD			
I PH	Preheat Time		2.4		sec	f _{Line} = 50Hz, GBD			
IGNITION	IGNITION Mode Characteristics								
V _{LOIGN+}	LO Pin Ignition Voltage Threshold		VCC		V	MODE = RE-IGN			
RUN Mod	e Characteristics								
VFBREG+	FB Pin Regulation Threshold	0.93	1.0	1.09	V				
VIGNDET+	FB Pin Ignition Detection Threshold	0.1	0.2	0.3	V				
VCO Cont	VCO Control Characteristics								
Ivco	VCO Charging Current	9.8	10.8	11.7	uA	MODE = IGN			
I _{VCO_ZVS}	ZVS VCO Discharging Current		400		uΛ				



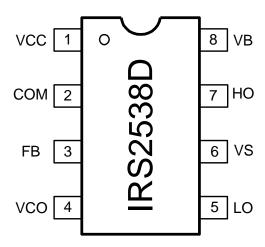
Electrical Characteristics

VCC=VBS=14V, VS=0V and TA = 25°C unless otherwise specified. The output voltage and current (VO and IO) parameters are referenced to COM and are applicable to the respective HO and LO output pins.

Symbol	Definition		Тур	Max	Units	Test Conditions			
Gate Driv	Gate Driver Output Characteristics (HO and LO)								
Voh_lo1	LO Leading Edge High-Level Output Voltage		12.6						
Voh_lo2	LO Steady State High-Level Output Voltage		10.8		V	I _O = 0A			
Vон_но	HO High-Level Output Voltage		VBS		V				
VoL	Low-Level Output Voltage		СОМ						
t _R	Output Rise Time		120		ns	CHO=1nF,			
tF	Output Fall Time		50		113	CLO=1nF			
I _{O+}	Output Source Current		180		mΛ				
Io-	Output Sink Current		260		mA				
Bootstrap FET Characteristics									
VB_ON	VB when the bootstrap FET is on		14.0		V	LO = 'HIGH'			
IB_CAP	VB source current when FET is on		23.0		mΛ	CBS = 0.1uF			
IB_10V	VB source current when FET is on		4.2		mA	VB = 10V			



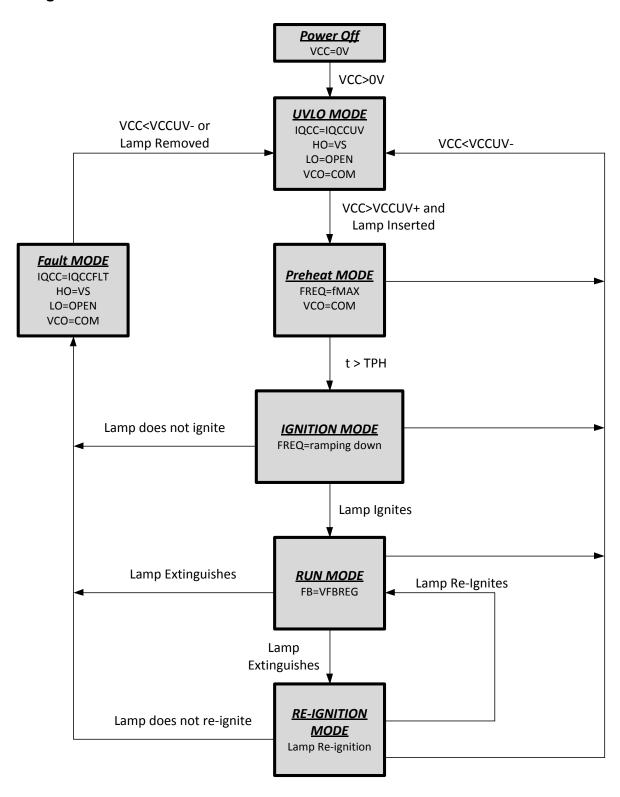
Pin Assignments and Definitions



Name	No.	Description			
VCC	1	Logic and internal gate drive supply voltage			
СОМ	2	IC power and signal ground			
FB	3	Lamp current feedback input			
VCO	4	Voltage-controlled oscillator (VCO) input			
LO	5	Half-bridge low-side gate driver output			
VS	6	High voltage floating supply return and half-bridge sensing input			
НО	7	High-side gate driver output			
VB	8	High-side gate driver floating supply			

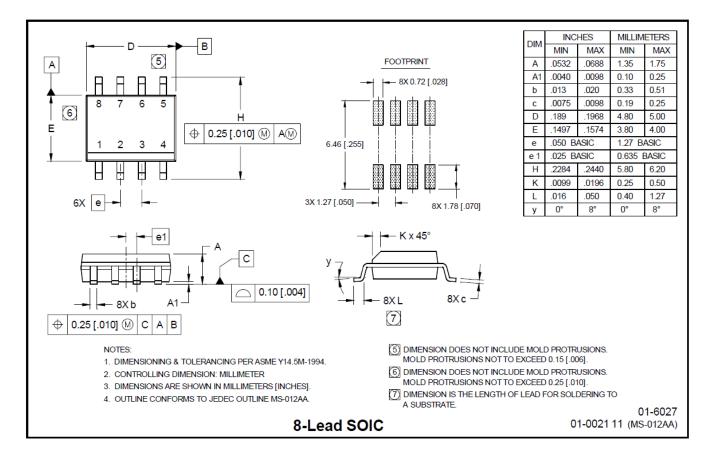


State Diagram



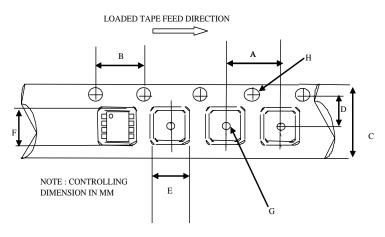


Package Details: SO8N



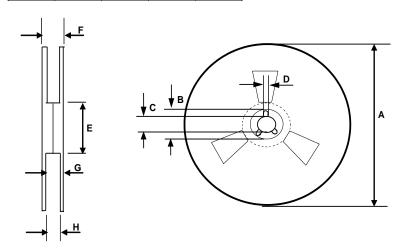


Tape and Reel Details: SO8N



CARRIER TAPE DIMENSION FOR 8SOICN

	Metric		Imperial		
Code	Min	Max	Min	Max	
Α	7.90	8.10	0.311	0.318	
В	3.90	4.10	0.153	0.161	
С	11.70	12.30	0.46	0.484	
D	5.45	5.55	0.214	0.218	
E	6.30	6.50	0.248	0.255	
F	5.10	5.30	0.200	0.208	
G	1.50	n/a	0.059	n/a	
Н	1.50	1.60	0.059	0.062	

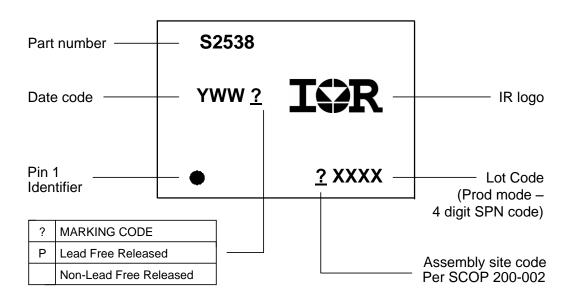


REEL DIMENSIONS FOR 8SOICN

	Metric		Imperial	
Code	Min	Max	Min	Max
Α	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566



Part Marking Information: SO8N



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